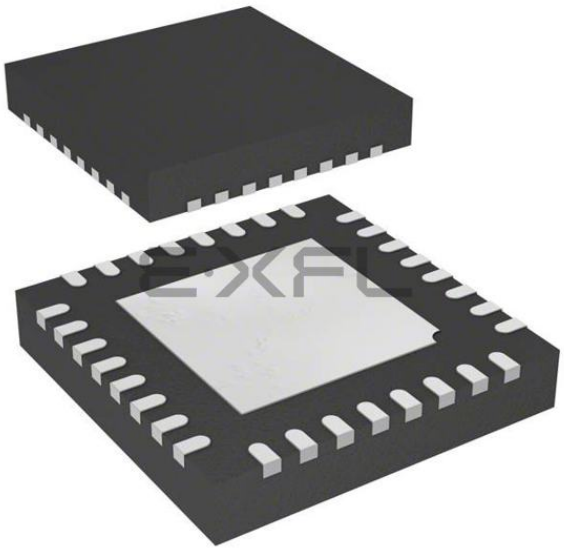


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	24
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 8x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302k8u6tr

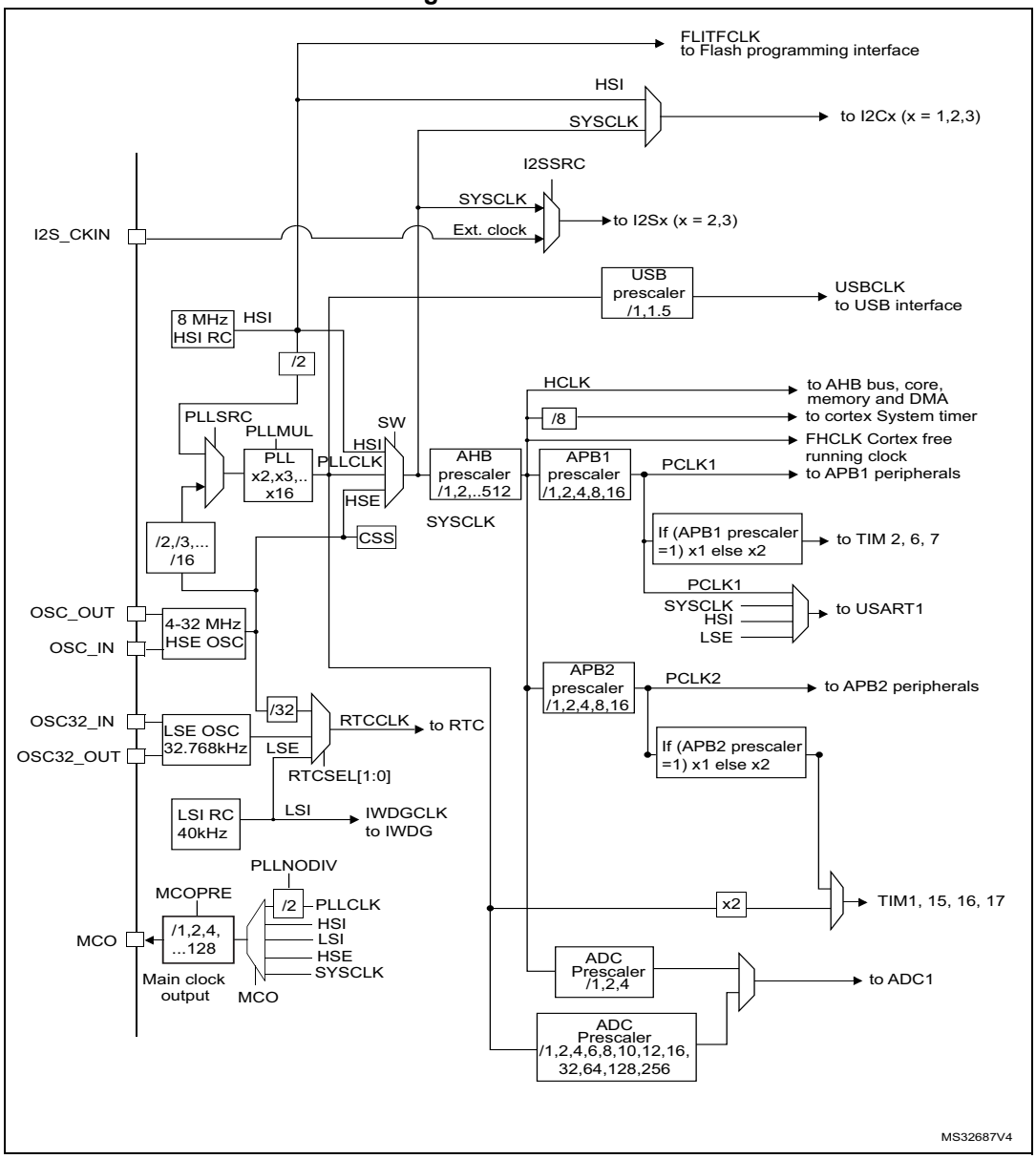
Contents

Table 1. STM32F302x6/8 device features and peripheral counts

Peripheral		STM32F302Kx		STM32F302Cx		STM32F302Rx	
Flash (Kbytes)		32	64	32	64	32	64
SRAM (Kbytes)		16					
Timers	Advanced control	1 (16-bit)					
	General purpose	3 (16-bit) 1 (32 bit)					
	Basic	1					
	SysTick timer	1					
	Watchdog timers (independent, window)	2					
	PWM channels (all)(1)	16		18			
	PWM channels (except complementary)	10		12			
Comm. interfaces	SPI/I2S	2					
	I^2C	3					
	USART	2		3			
	USB 2.0 FS	1					
	CAN 2.0B	1					
GPIOs	Normal I/Os (TC, TTa)	9		20		26	
	5-Volt tolerant I/Os (FT, FT1)	15		17		25	
DMA channels		7					
Capacitive sensing channels		13		17		18	
12-bit ADC Number of channels		1 8		1 11		1 15	
12-bit DAC channels		1					
Analog comparator		2		3		3	
Operational amplifier		1					
CPU frequency		72 MHz					
Operating voltage		2.0 to 3.6 V					
Operating temperature		Ambient operating temperature: - 40 to 85 °C / - 40 to 105 °C Junction temperature: - 40 to 125 °C					
Packages		UFQFPN32		LQFP48, WLCSP49		LQFP64	

1. This total number considers also the PWMs generated on the complementary output channels.

Figure 2. Clock tree



The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms with wake up from Stop and Standby mode capability.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy.
- Two anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.
- 17-bit Auto-reload counter for periodic interrupt with wakeup from STOP/STANDBY capability.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 40 kHz)
- The high-speed external clock divided by 32.

mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

Refer to *Table 8* for the features available in SPI2 and SPI3.

Table 8. STM32F302x6/8 SPI/I2S implementation

SPI features(1)	SPI2	SPI3
Hardware CRC calculation	X	X
Rx/Tx FIFO	X	X
NSS pulse mode	X	X
I2S mode	X	X
TI mode	X	X

1. X = supported.

3.20 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.21 Universal serial bus (USB)

The STM32F302x6 STM32F302x8 embeds a full-speed USB device peripheral compliant with the USB specification version 2.0. The USB interface implements a full-speed (12 Mbit/s) function interface with added support for USB 2.0 Link Power Management. It has software-configurable endpoint setting with packet memory up-to 1 KB (the last 256 bytes are used for CAN peripheral if enabled) and suspend/resume support. It requires a precise 48 MHz clock which is generated from the internal main PLL (the clock source must use an HSE crystal oscillator).

3.22 Touch sensing controller (TSC)

The STM32F302x6/8 devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 18 capacitive sensing channels distributed over 6 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (for example glass, plastic). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate.

Table 12. STM32F302x6/8 pin definitions

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
-	B6	1	1	VBAT	S	-	-	Backup power supply	
-	D5	2	2	PC13(1) TAMPER1 WKUP2 (PC13)	I/O	TC	(1)	TIM1_CH1N	WKUP2, RTC_TAMP1, RTC_TS, RTC_OUT
-	C7	3	3	PC14(1) OSC32_IN (PC14)	I/O	TC	(1)	-	OSC32_IN
-	C6	4	4	PC15(1) OSC32_OUT (PC14)	I/O	TC	(1)	-	OSC32_OUT
2	D7	5	5	PF0 OSC_IN (PF0)	I/O	FTf	-	I2C2_SDA, SPI2_NSS/I2S2_WS, TIM1_CH3N	OSC_IN
3	D6	6	6	PF1 OSC_OUT (PF1)	O	FTf	-	I2C2_SCL, SPI2_SCK/I2S2_CK	OSC_OUT
4	E7	7	7	NRST	I/O	RST	-	Device reset input/internal reset output (active low)	
-	-	-	8	PC0	I/O	TTa	-	EVENTOUT, TIM1_CH1	ADC1_IN6
-	-	-	9	PC1	I/O	TTa	-	EVENTOUT, TIM1_CH2	ADC1_IN7
-	-	-	10	PC2	I/O	TTa	-	EVENTOUT, TIM1_CH3	ADC1_IN8
-	-	-	11	PC3	I/O	TTa	-	EVENTOUT, TIM1_CH4, TIM1_BKIN2	ADC1_IN9
6	E6	8	12	VSSA/VREF-	S	-	-	Analog ground/Negative reference voltage	
5	A6	9	13	VDDA/VREF+	S	-	-	Analog power supply/Positive reference voltage	

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = V_{DDA}= 3.3 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 9*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 10*.

Figure 9. Pin loading conditions

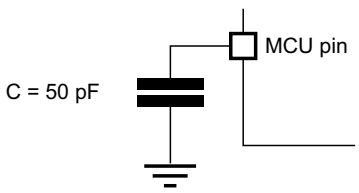
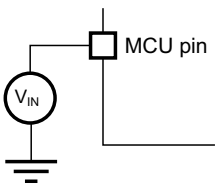


Figure 10. Pin input voltage



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 19: Voltage characteristics*, *Table 20: Current characteristics*, and *Table 21: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 19. Voltage characteristics(1)

Symbol	Ratings	Min	Max	Unit
V_{DD}–V_{SS}	External main supply voltage (including V_{DDA}, V_{BAT} and V_{DD})	-0.3	4.0	V
V_{DD}–V_{DDA}	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V
V_{IN}(2)	Input voltage on FT and FTf pins	V_{SS} −0.3	V_{DD} + 4.0	V
	Input voltage on TTa and TT pins	V_{SS} −0.3	4.0	
	Input voltage on any other pin	V_{SS} −0.3	4.0	
	Input voltage on Boot0 pin	0	9	
$\lvert\Delta V_{DDx}\rvert$	Variations between different V_{DD} power pins	-	50	mV
$\lvert V_{SSX} - V_{SS}\rvert$	Variations between all the different ground pins(3)	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.12: Electrical sensitivity characteristics*		V

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range. The following relationship must be respected between V_{DDA} and V_{DD}:
V_{DDA} must power on before or at the same time as V_{DD} in the power up sequence.
V_{DDA} must be greater than or equal to V_{DD}.
2. V_{IN} maximum must always be respected. Refer to *Table 20: Current characteristics* for the maximum allowed injected current values.
3. Include V_{REF-} pin.

Table 20. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all VDD_x power lines (source)	130	mA
ΣI_{VSS}	Total current out of sum of all VSS_x ground lines (sink)	-130	
I_{VDD}	Maximum current into each V_{DD_x} power line (source)(1)	100	
I_{VSS}	Maximum current out of each V_{SS_x} ground line (sink)(1)	-100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/O and control pin	-25	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins(2)	80	
	Total output current sourced by sum of all IOs and control pins(2)	-80	
$I_{INJ(PIN)}$	Injected current on TT, FT, FTf and B pins(3)	-5/+0	
	Injected current on TC and RST pin(4)	+/-5	
	Injected current on TTa pins(5)	+/-5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(6)	+/-25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS} and V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins.The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 19: Voltage characteristics* for the maximum allowed input voltage values.
5. A positive injection is induced by $V_{IN} > V_{DDA}$ while a negative injection is induced by $V_{IN} < V_{SS}$. I_{INJ}(PIN) must never be exceeded. Refer also to *Table 19: Voltage characteristics* for the maximum allowed input voltage values. Negative injection disturbs the analog performance of the device. See note (2) below *Table 68*.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 21. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 22. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	72	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	36	
f_{PCLK2}	Internal APB2 clock frequency	-	0	72	
V_{DD}	Standard operating voltage	-	2	3.6	V
V_{DDA}	Analog operating voltage (OPAMP and DAC not used)	Must have a potential equal to or higher than V_{DD}	2	3.6	V
	Analog operating voltage (OPAMP and DAC used)		2.4	3.6	
V_{BAT}	Backup operating voltage	-	1.65	3.6	V
V_{IN}	I/O input voltage	TC I/O	–0.3	V_{DD}+0.3	V
		TT I/O(1)	-0.3	3.6	
		TTa I/O pins	–0.3	V_{DDA}+0.3	
		FT and FTf I/O(1)	–0.3	5.5	
		BOOT0	0	5.5	
P_D	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(2)	LQFP64	-	444	mW
		LQFP48	-	364	
		WLCSP49	-	408	
		UFQFPN32	-	540	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	–40	85	°C
		Low power dissipation(3)	–40	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	105	°C
		Low power dissipation(3)	–40	125	
T_J	Junction temperature range	6 suffix version	–40	105	°C
		7 suffix version	–40	125	

1. To sustain a voltage higher than V_{DD}+0.3 V, the internal pull-up/pull-down resistors must be disabled.
2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax}. See *Table 82: Package thermal characteristics*.
3. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax}. See *Table 82: Package thermal characteristics*

6.3.4 Embedded reference voltage

The parameters given in *Table 26* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 26. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.20	1.23	1.25	V
$T_{S\_vrefint}$	ADC sampling time when reading the internal reference voltage	-	2.2	-	-	µs
V_{RERINT}	Internal reference voltage spread over the temperature range	V_{DD} = 3 V ±10 mV	-	-	10(1)	mV
T_{Coeff}	Temperature coefficient	-	-	-	100 (1)	ppm/°C

1. Guaranteed by design.

Table 27. Internal reference voltage calibration values

Calibration value name	Description	Memory address
V_{REFINT_CAL}	Raw data acquired at temperature of 30 °C V_{DDA}= 3.3 V	0x1FFF F7BA - 0x1FFF F7BB

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.
The current consumption is measured as described in *Figure 12: Current consumption measurement scheme*.
All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Note: The total current consumption is the sum of I_{DD} and I_{DDA}.

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 41*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 41. HSE oscillator characteristics

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	During startup(3)	-	-	8.5	mA
		V_{DD}=3.3 V, Rm= 30Ω, CL=10 pF@8 MHz	-	0.4	-	
		V_{DD}=3.3 V, Rm= 45Ω, CL=10 pF@8 MHz	-	0.5	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL= 5 pF@32 MHz	-	0.8	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL=10 pF@32 MHz	-	1	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL=20 pF@32 MHz	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 42*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 42. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
I_{DD}	LSE current consumption	LSEDRV[1:0]=00 lower driving capability	-	0.5	0.9	µA
		LSEDRV[1:0]=10 medium low driving capability	-	-	1	
		LSEDRV[1:0]=01 medium high driving capability	-	-	1.3	
		LSEDRV[1:0]=11 higher driving capability	-	-	1.6	
g_m	Oscillator transconductance	LSEDRV[1:0]=00 lower driving capability	5	-	-	µA/V
		LSEDRV[1:0]=10 medium low driving capability	8	-	-	
		LSEDRV[1:0]=01 medium high driving capability	15	-	-	
		LSEDRV[1:0]=11 higher driving capability	25	-	-	
$t_{SU(LSE)}$(3)	Startup time	V_{DD} is stabilized	-	2	-	s

1. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
2. Guaranteed by design.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Low-speed internal (LSI) RC oscillator

Table 44. LSI oscillator characteristics(1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	50	kHz
$t_{su(LSI)}$(2)	LSI oscillator startup time	-	-	85	µs
$I_{DD(LSI)}$(2)	LSI oscillator power consumption	-	0.75	1.2	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design.

6.3.9 PLL characteristics

The parameters given in *Table 45* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22*.

Table 45. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max	
f_{PLL_IN}	PLL input clock(1)	1(2)	-	24(2)	MHz
	PLL input clock duty cycle	40(2)	-	60(2)	%
f_{PLL_OUT}	PLL multiplier output clock	16(2)	-	72	MHz
t_{LOCK}	PLL lock time	-	-	200(2)	µs
Jitter	Cycle-to-cycle jitter	-	-	300(2)	ps

1. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.
2. Guaranteed by design.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 23* and *Table 55*, respectively.

Unless otherwise specified, the parameters given are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 55. I/O AC characteristics(1)

OSPEEDRy [1:0] value(1)	Symbol	Parameter	Conditions	Min	Max	Unit
x0	$f_{max(IO)out}$	Maximum frequency(2)	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	2(3)	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	125(3)	ns
	$t_{r(IO)out}$	Output low to high level rise time		-	125(3)	
01	$f_{max(IO)out}$	Maximum frequency(2)	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	10(3)	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	25(3)	ns
	$t_{r(IO)out}$	Output low to high level rise time		-	25(3)	
11	$f_{max(IO)out}$	Maximum frequency(2)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	50(3)	MHz
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30(3)	MHz
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	-	20(3)	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	5(3)	ns
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	8(3)	
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	-	12(3)	
	$t_{r(IO)out}$	Output low to high level rise time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	5(3)	
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	8(3)	
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	-	12(3)	
FM+ configuration(4)	$f_{max(IO)out}$	Maximum frequency(2)	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	2(4)	MHz
	$t_{f(IO)out}$	Output high to low level fall time		-	12(4)	ns
	$t_{r(IO)out}$	Output low to high level rise time		-	34(4)	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-‘	ns

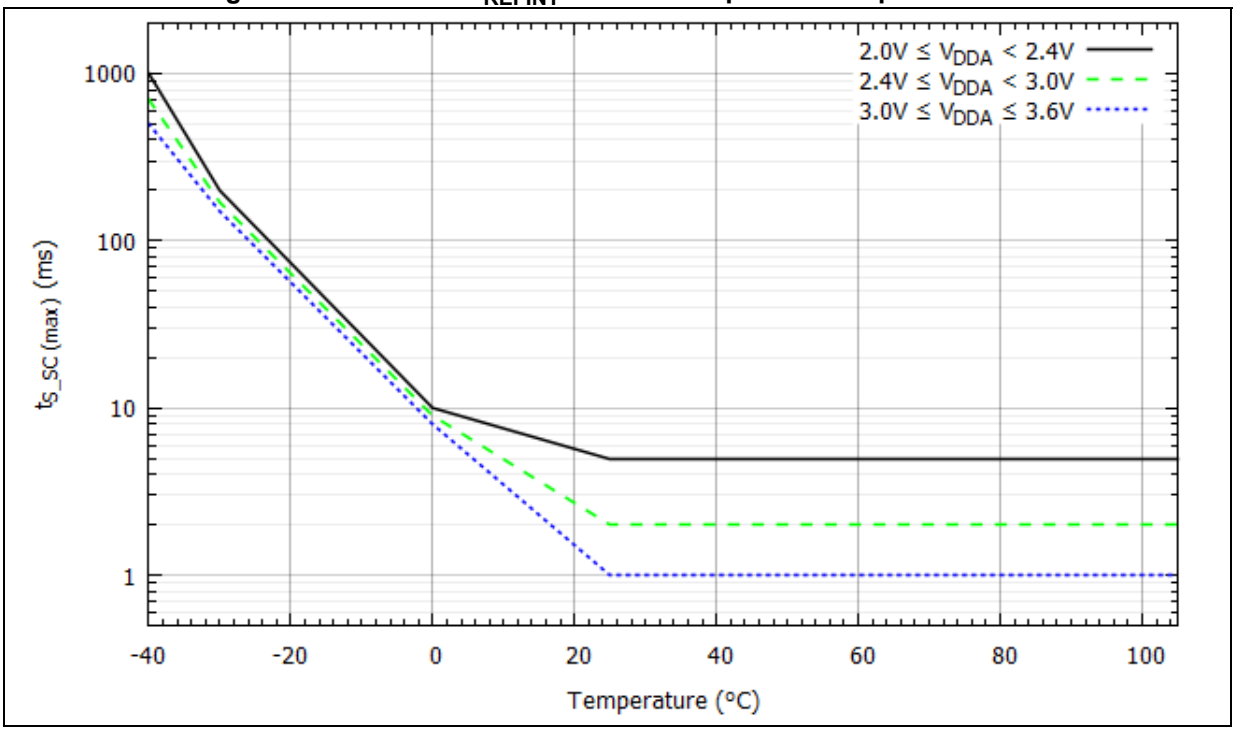
1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the RM0365 reference manual for a description of GPIO Port configuration register.
2. The maximum frequency is defined in *Figure 23*.
3. Guaranteed by design.
4. The I/O speed configuration is bypassed in FM+ I/O mode. Refer to the STM32F302x6 STM32F302x8 reference manual RM0365 for a description of FM+ I/O mode configuration.

Table 72. Comparator characteristics(1)(2) (continued)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{S_SC}	V_{REFINT} scaler startup time from power down	V_{REFINT} scaler activation after device power on	-	-	1(3)	s
		Next activations	-	-	0.2	ms
t_{START}	Comparator startup time	$V_{DDA} \geq 2.7$ V	-	-	4	µs
		$V_{DDA} < 2.7$ V	-	-	10	
t_D	Propagation delay for 200 mV step with 100 mV overdrive	$V_{DDA} \geq 2.7$ V	-	25	28	ns
		$V_{DDA} < 2.7$ V	-	28	30	
	Propagation delay for full range step with 100 mV overdrive	$V_{DDA} \geq 2.7$ V	-	32	35	
		$V_{DDA} < 2.7$ V	-	35	40	
V_{OFFSET}	Comparator offset error	$V_{DDA} \geq 2.7$ V	-	±5	±10	mV
		$V_{DDA} < 2.7$ V	-	-	±25	
TV_{OFFSET}	Total offset variation	Full temperature range	-	-	3	mV
$I_{DD(COMP)}$	COMP current consumption	-	-	400	600	µA

1. Guaranteed by design.
2. The comparators do not have built-in hysteresis.
3. For more details and conditions, see *Figure 35: Maximum VREFINT scaler startup time from power down*.

Figure 35. Maximum V_{REFINT} scaler startup time from power down



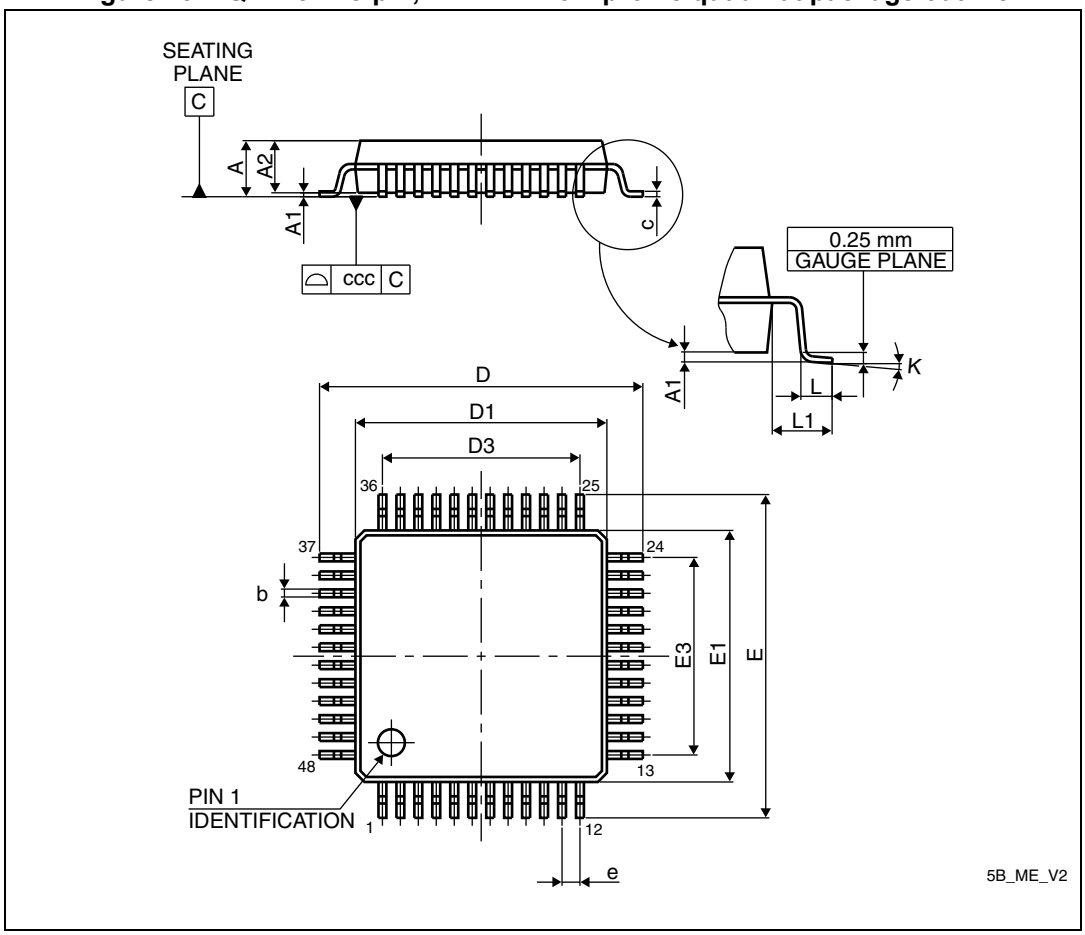
6.3.21 Operational amplifier characteristics

Table 73. Operational amplifier characteristics(1)

Symbol	Parameter		Condition	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage		-	2.4	-	3.6	V
CMIR	Common mode input range		-	0	-	V_{DDA}	V
VI_{OFFSET}	Input offset voltage	Maximum calibration range	25°C, No Load on output.	-	-	4	mV
			All voltage/Temp.	-	-	6	
		After offset calibration	25°C, No Load on output.	-	-	1.6	
			All voltage/Temp.	-	-	3	
ΔVI_{OFFSET}	Input offset voltage drift		-	-	5	-	µV/°C
I_{LOAD}	Drive current		-	-	-	500	µA
IDDOPAMP	Consumption		No load, quiescent mode	-	690	1450	µA
CMRR	Common mode rejection ratio		-	-	90	-	dB
PSRR	Power supply rejection ratio		DC	73	117	-	dB
GBW	Bandwidth		-	-	8.2	-	MHz
SR	Slew rate		-	-	4.7	-	V/µs
R_{LOAD}	Resistive load		-	4	-	-	kΩ
C_{LOAD}	Capacitive load		-	-	-	50	pF
VOH_{SAT}	High saturation voltage(2)		R_{load} = min, Input at V_{DDA}.	V_{DDA}-100	-	-	mV
			R_{load} = 20K, Input at V_{DDA}.	V_{DDA}-20	-	-	
VOL_{SAT}	Low saturation voltage(2)		Rload = min, input at 0V	-	-	100	
			Rload = 20K, input at 0V.	-	-	20	
φm	Phase margin		-	-	62	-	°
$t_{OFFTRIM}$	Offset trim time: during calibration, minimum time needed between two steps to have 1 mV accuracy		-	-	-	2	ms
t_{WAKEUP}	Wake up time from OFF state.		C_{LOAD} ≤50 pf, R_{LOAD} ≥ 4 kΩ, Follower configuration	-	2.8	5	µs
$t_{S\_OPAM\_VOUT}$	ADC sampling time when reading the OPAMP output			400	-	-	ns

7.3 LQFP48 package information

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline

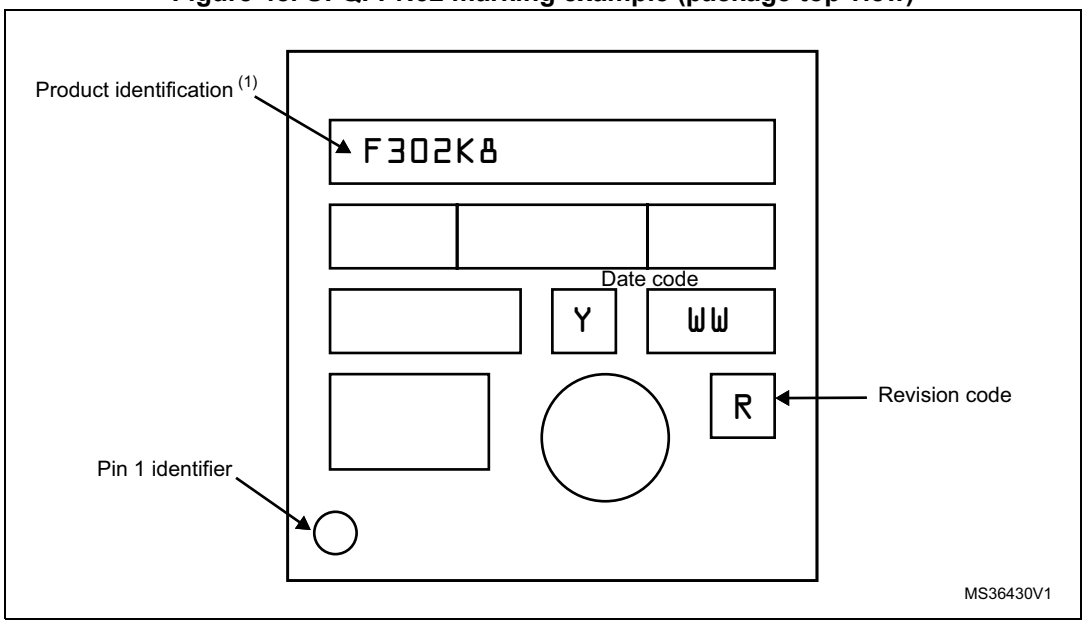


1. Drawing is not to scale.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 48. UFQFPN32 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.